





RELEASE A DATA SHEET

FEATURES

- Flexible Bias
- \bullet Internally Matched to 50 Ω
- Process: GaAs pHEMT
- Compact 1.5 x 1.5 mm DFN-6 Package

AEC-Q100 Grade 2 Qualified

- 100% Device Reflow at Assembly
- 100% Optical Die Inspection

Reference: 5 V / 90 mA / 0.9 GHz

Gain: 14.8 dBOIP3: 40 dBmOP1dB: 23 dBm

• Evaluation Board Noise Figure: 2.7 dB

Reference: 8 V / 100 mA / 0.9 GHz

Gain: 14.9 dBOIP3: 40 dBmOP1dB: 25 dBm

• Evaluation Board Noise Figure: 2.8 dB

APPLICATIONS

- Cellular Boosters (compensators)
- Linear Driver Amplifiers



M DESCRIPTION

The GRF2012W is a broadband gain block with low noise figure (NF) and industry leading linearity designed for small cell, wireless infrastructure and other high-performance applications. It exhibits outstanding broadband NF and linearity over 700 to 3800 MHz with a single match.

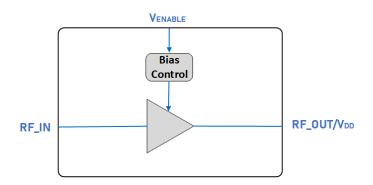
The device is operated from a supply voltage of 2.7 to 8 V with a selectable $I_{\rm DDQ}$ range of 15 to 100 mA for optimal efficiency and linearity.

The GRF2012W is internally matched to 50 Ω at the input and output ports needing only an external DC block on the input and a bias choke on the output.

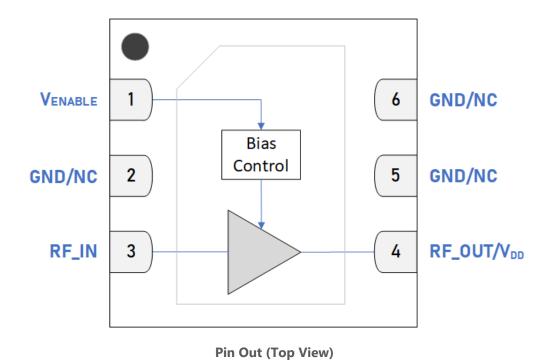
Please consult with the GRF applications engineering team for custom tuning/evaluation board data and device S-parameters.

Additional tunes can be found on the GRF2012W "Custom Tunes" product page: GRF2012W Custom Tunes

M BLOCK DIAGRAM









Pin Assignments

Pin	Name	Description	Note
1	V _{ENABLE}	Enable Voltage Input	V_{ENABLE} and series resistor set I_{DDQ} . $V_{ENABLE} \le 0.2$ volts disables the device.
2, 5, 6	GND/NC	Ground or No Connect	No internal connection to die.
3	RF_IN	LNA RF Input	Internally matched to 50 Ω . An external DC blocking capacitor must be used.
4	RF_OUT/V _{DD}	LNA RF Output	Internally matched to 50 Ω . V_{DD} must be applied through an RF choke to this pin.
PKG BASE	GND	Ground	Provides DC and RF ground for LNA, as well as thermal heat sink. Recommend multiple 8 mil vias beneath the package for optimal RF and thermal performance. Refer to evaluation board top layer graphic on schematic page.



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Absolute Ratings

Parameter	Symbol	Min.	Max.	Unit
Supply Voltage	V _{DD}	0	9	V
RF Input Power: Load VSWR < 2:1, V _{DD} ≤ 8 V	P _{IN MAX}		22	dBm
Operating Temperature (Package Base)	T _{PKG BASE}	-40	105	°C
Maximum Channel Temperature (MTTF > 106 Hours)	T _{MAX}		170	°C
Maximum Dissipated Power	P _{DISS MAX}		1	W

Electrostatic Discharge

Human Body Model	НВМ	250		V
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Storage

Storage Temperature	T _{STG}	-65	150	°C
Moisture Sensitivity Level	MSL		1	



Caution! ESD Sensitive Device.

Exceeding Absolute Maximum Rating conditions may cause permanent damage.

Note: For additional information, please refer to Manufacturing Note MN-001 - Packaging and Manufacturing Information.



All Guerrilla RF products are provided in RoHS compliant lead (Pb)-free packaging. For additional information, please refer to the Certificate of RoHS Compliance.





Recommended Operating Conditions

Parameter	Symbol	Sp	Specification			Condision
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Supply Voltage	V _{DD}	0	5	9	V	
Operating Temperature (Package Base)	T _{PKG BASE}	-40		105	°C	
RF Frequency Range	F _{TEST}	0.05	0.9	6	GHz	Typical application schematic with external matching components (notes 1 & 2).
RF_IN Port Impedance	Z _{RFIN}		50		Ω	Single ended.
RF_OUT Port Impedance	Z _{RFOUT}		50		Ω	Single ended.

Note 1: Operation outside of this range is supported by using different custom tunes. Examples of other optimized tunes can be found here: GRF2012W Custom Tunes

Note 2: Contact the Guerrilla RF Applications team for guidance on optimizing the tuning of the device for alternative bands.





Nominal Operating Parameters - General

The following conditions apply unless noted otherwise: typical measurement schematic using the 0.05 to 6 GHz tuning set, 50 Ω system impedance, M5 = 300 Ω , V_{DD} = 5 V, V_{ENABLE} = 5 V, I_{DD} = 90 mA, F_{TEST} = 0.9 GHz, T_{PKG BASE} = 25 °C. Evaluation board losses are included within the specifications.

Parameter	Symbol	Sp	ecification	ification		Condition
Farameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Switching Rise Time	T _{RISE}		200		ns	
Switching Fall Time	T _{FALL}		300		ns	
Supply Current	I _{DD}	80	94	108	mA	$V_{DD} = V_{ENABLE} = 5 \text{ V}, R_{BIAS} = 300 \Omega$
Enable Current	I _{ENABLE}		5	8	mA	

Disabled Mode

Leakage Current	I _{LEAKAGE}	110	300	μΑ	$V_{DD} = 5 \text{ V}, V_{ENABLE} = 0 \text{ V}.$

Thermal Data

Thermal Resistance (Infrared Scan)	Θ _{ЈС}	55	°C/W	On standard evaluation board. No RF applied. Note 3.
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Note 3: MTTF > 10^6 hours for $T_{CHANNEL} < 170$ °C.





GRF2012W BROADBAND LINEAR GAIN BLOCK 0.03 (0 0 GHZ

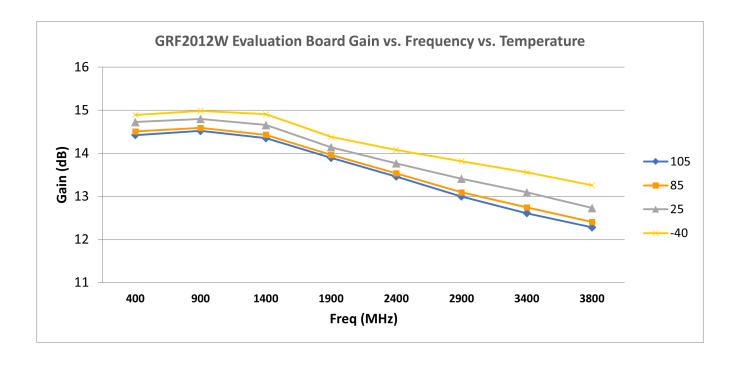
Nominal Operating Parameters - RF

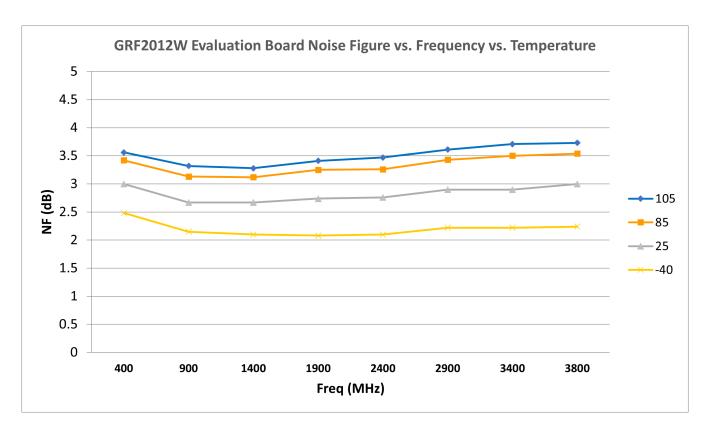
The following conditions apply unless noted otherwise: typical measurement schematic using the 0.05 to 6 GHz tuning set, 50 Ω system impedance, M5 = 300 Ω , V_{DD} = 5 V, V_{ENABLE} = 5 V, I_{DD} = 90 mA, F_{TEST} = 0.9 GHz, T_{PKG BASE} = 25 °C. Evaluation board losses are included within the specifications.

Parameter	Symbol	Specification			Unit	Condition
Parameter	Symbol	Min.	Тур.	Max.	Onit	Condition
Gain	S21	13.8	14.8	16.5	dB	
Reverse Isolation	S12		< -20		dB	F _{RF} = 0.4 to 3.8 GHz.
Noise Figure	NF		2.7	2.95	dB	On standard evaluation board.
Output 3rd Order Intercept Point	OIP3		40		dBm	2 dBm P _{OUT} per tone at 2 MHz spacing (899 and 901 MHz).
Output 1 dB Compression Power	OP1dB	21.5	23		dBm	



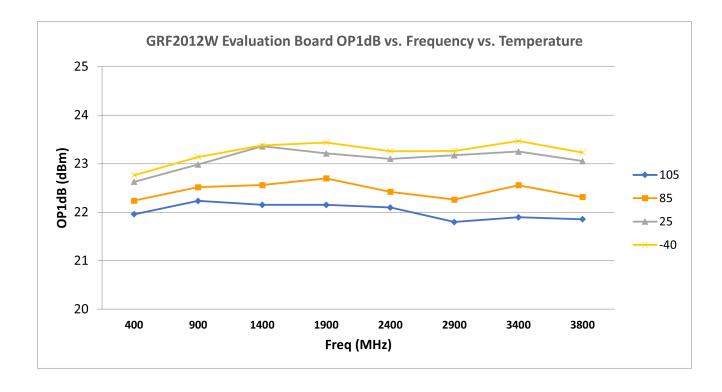
GRF2012W Typical Operating Curves: 0.4 to 3.8 GHz Tune

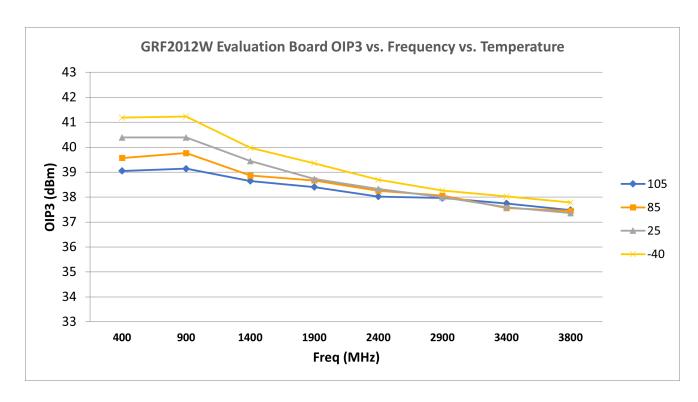




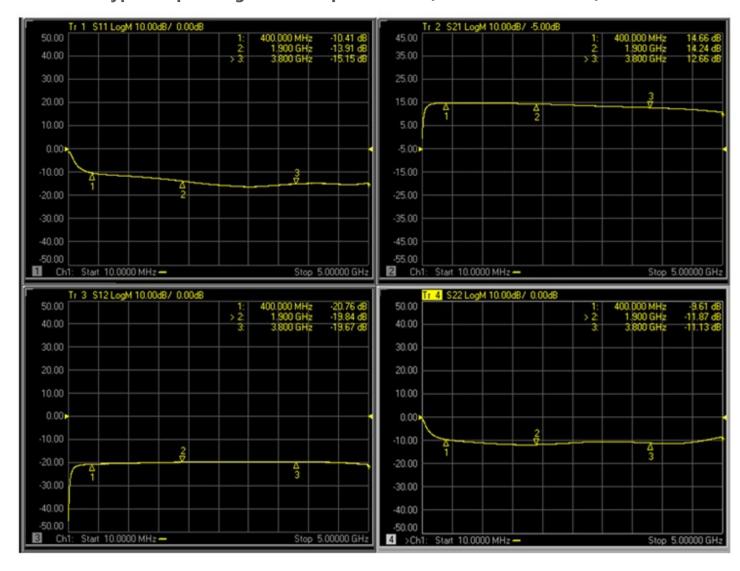


GRF2012W Typical Operating Curves: 0.4 to 3.8 GHz



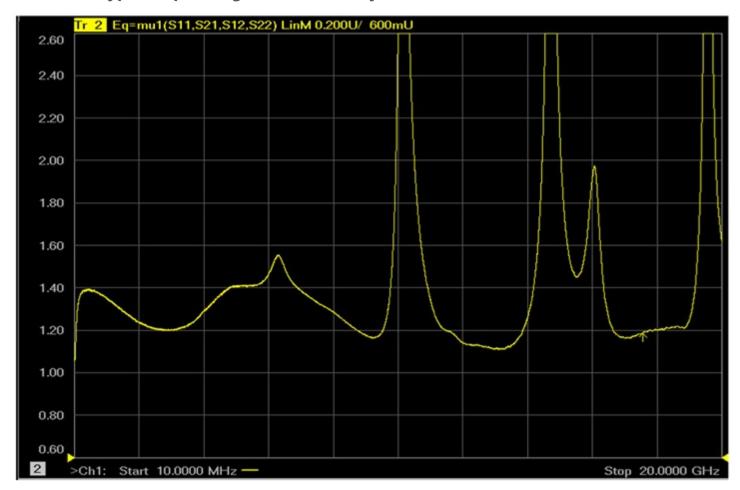


GRF2012W Typical Operating Curves: S-parameters (0.4 to 3.8 GHz Tune)



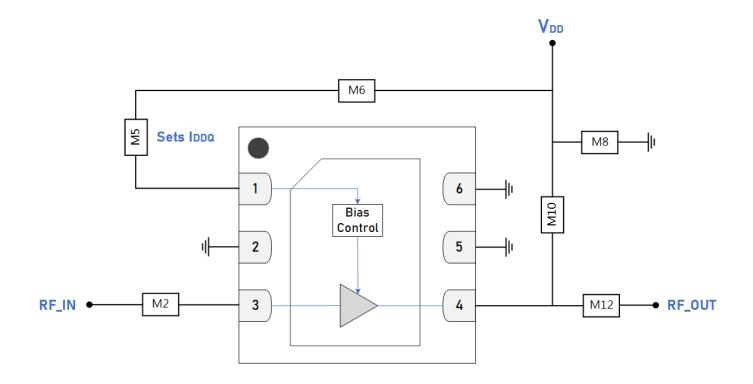


GRF2012W Typical Operating Curves: Stability Mu Factor (10 MHz to 20 GHz)

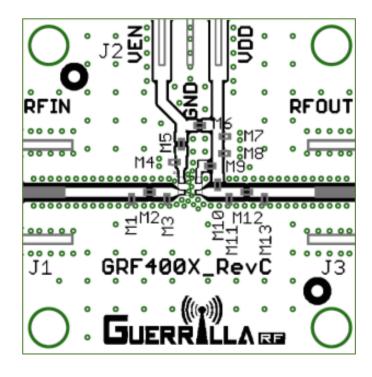


Note: Mu prime factor ≥ 1.0 implies unconditional stability.





GRF2012W Standard Evaluation Board Schematic



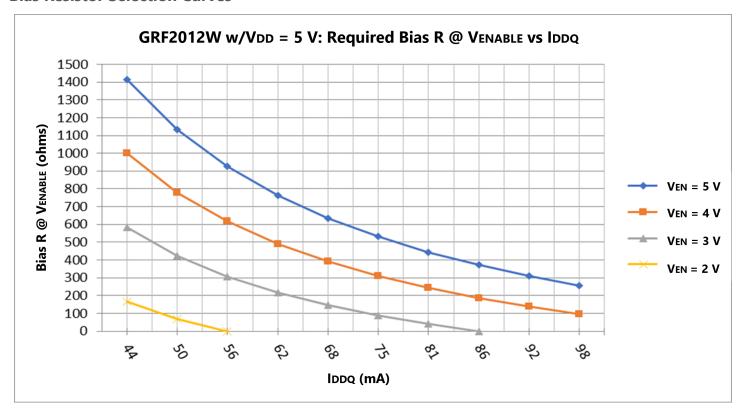
GRF2012W Evaluation Board Assembly Diagram



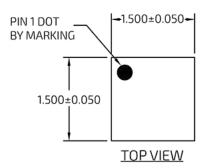
GRF2012W Evaluation Board Assembly Diagram Reference: 0.4 to 3.8 GHz Tune

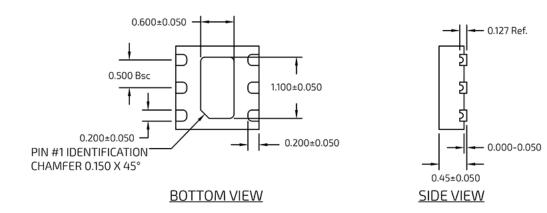
Component	Туре	Manufacturer	Family	Value	Package Size	Substitution
M2	Capacitor	Murata	GRM	100 pF	0402	ok
M5 (sets I _{DDQ})	Resistor	Various	5%	see curves	0402	ok
M6	Resistor (jumper)	Various	5%	0 Ω	0402	ok
M8	Capacitor	Murata	GRM	0.1 μF	0402	ok
M10	Inductor	Murata	LQG	47 nH	0402	ok
M12	Capacitor	Murata	GRM	1000 pF	0402	ok
Evaluation Board	GRF400X_RevC					

Bias Resistor Selection Curves



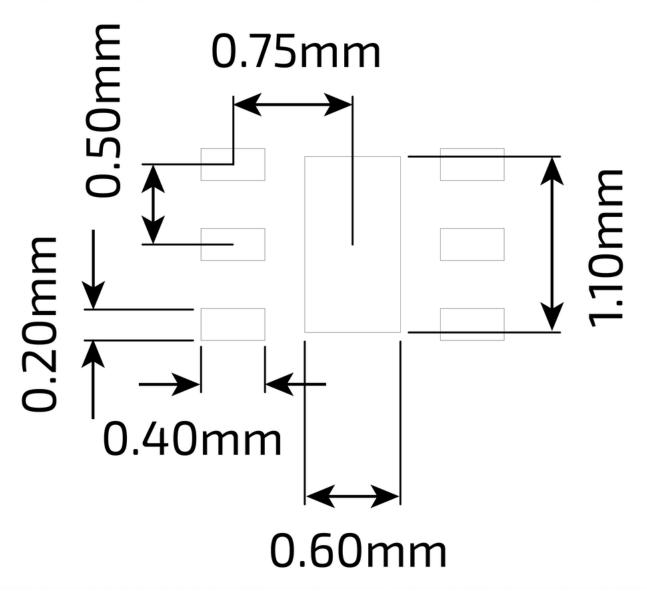






DFN 6 1.5x1.5mm Package Dimensions





DFN 6 1.5x1.5mm Suggested PCB Footprint (Top View)



Package Marking Diagram

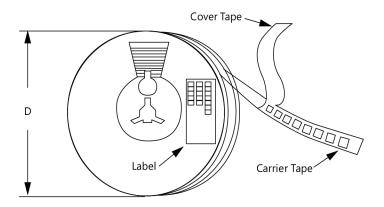


Line 1: "Y" = YEAR (single digit). "WW" = WORK WEEK and "w" = W for automotive.

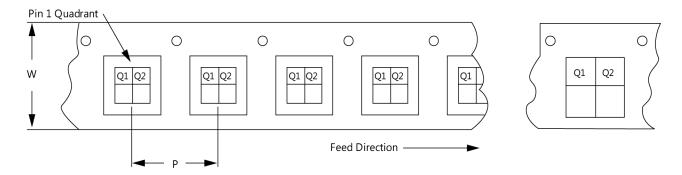
Line 2: "XXXX" = Device Part Number.

Tape and Reel Information

Guerrilla RF's tape and reel specification complies with Electronics Industries Association (EIA) standards for "Embossed Carrier Tape of Surface Mount Components for Automatic Handling" (reference EIA-481). Devices are loaded with pins down into the carrier pocket with protective cover tape and reeled onto a plastic reel. Each reel is packaged in a cardboard box. There are product labels on the reel, the protective ESD bag, and the outside surface of the box. For the latest reel specifications and package information (including units/reel), please visit Package Manufacturing Information | Guerrilla RF (querrilla-rf.com).



Tape and Reel Packaging with Reel Diameter Noted (D)



Carrier Tape Width (W), Pitch (P), Feed Direction and Pin 1 Quadrant Information



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Revision History

Revision Date	Description of Change
January 9, 2019	Preliminary Data Sheet.
October 19, 2019	Release Ø Data Sheet.
February 14, 2022	Removed CDM parameter from absolute ratings table.
September 20, 2022	Release A Data Sheet. Upgraded Data Sheet to new format.
May 22, 2024	Upgraded Data Sheet to newest format only.



RELEASE A DATA SHEET

Data Sheet Classifications

Data Sheet Status	Notes
Advance	S-parameter and NF data based on EM simulations for the fully packaged device using foundry-supplied transistor S-parameters. Linearity estimates based on device size, bias condition and experience with related devices.
Preliminary	All data based on evaluation board measurements taken within the Guerrilla RF Applications Lab. Any MIN/MAX limits represented within the data sheet are based solely on <i>estimated</i> part-to-part variations and process spreads. All parametric values are subject to change pending the collection of additional data.
Release Ø	All data based on measurements taken with <i>production-released</i> material. TYP values are based on a combination of ATE and bench-level measurements, with MIN/MAX limits defined using <i>modelled estimates</i> that account for part-to-part variations and expected process spreads. Although unlikely, future refinements to the TYP/MIN/MAX values may be in order as multiple lots are processed through the factory.
Release A-Z	All data based on measurements taken with production-released material derived from multiple lots which have been fabricated over an extended period of time. MIN/MAX limits may be refined over previous releases as more statistically significant data is collected to account for process spreads.

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